NSN 5962-01-269-1016

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Unit Of Measure	
N/a	
Shelf Life:	
16 printed circuit	
Terminal Type	And Quantity:
96906-mil-std-88	3 standard (includes industry or association standards, individual manufactureer standards, etc.).
Test Data Docu	ment:
Rom	
Memory Device	Туре:
output	
80.00 nanoseco	nds propagation delay time, low to high level output and 80.00 nanoseconds propagation delay time, high to low I
Time Rating Pe	r Chacteristic:
-0.5 volts power	source and 7.0 volts power source
Voltage Rating	And Type Per Characteristic:
Solder	
Terminal Surfac	e Treatment:
D-2 mil-m-38510	-
-	ource And Designator:
6 input	
Input Circuit Pa	
Transistor-transi	
Output Logic F	orm:
Dual-in-line	
Inclosure Confi	guration:
Ceramic	
Inclosure Mater	
	ogrammable and bipolar and 3-state output
Features Provid	
-65.0/+150.0 deg	
-55.0/+125.0 deo Storage Tempu	
	burature Range:
739.0 milliwatts	r Dissipation Rating:
0.140 inches	
Body Height:	
	nches and 0.310 inches
Body Width:	
0.840 inches	

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Yes - demil/mli
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